

Features

- Bi-directional crowbar transient voltage protection
- High surge capability
- High off-state impedance
- Low leakage current
- Low on-state voltage
- Short-circuit failure mode

Main Application

BORN's thyristor surge protector devices are designed to help protect sensitive telecommunication equipment from the hazards caused by lighning ,power contact, and power induction. These devices enable equipment to comply with various regulatory requirements including GR 1089,ITU K.20,K.21 and K.45,IEC 60950,UL 60950,and TIA-968-A(formerly known as FCC Part 68).

Typical application including:

- Central office switching equipment. Analog and digital linecards(xDSL,T1/E1,ISDN.....)
- Customer Premises Equipment (CPE) such as phones, fax machines, modems, POS terminals, PBX systems and caller ID adjunct boxes.
- Primary protection modules including Main Distribution Frames(MDF), building entrance equipment and station protection modules.
- Access network equipment such as remote terminals, line repeaters, multiplexers, cross-connects, WAN equipment, Network Interface Devices (NID).
- Data lines and security systems.
- CATV line amplifiers and power inserters.
- Sprinkler systems.

Electrcal Parameters (Tamb=25°C)

Part Number	VDRM	IDRM	Vво	Іво	VT	Іт	Со	`Ін
	Min.	Max.	Max.	Max.	Max.	Max.	Max.	Min.
	V	uA	V	mA	V	А	pF	mA
BEP0080MA	6	5	25	800	4	2.2	50	50



ROHS 🍗

Eletrical Characteristics

VDRM	Stand-off voltage, is measured at IDRM	Ін	Holding current.
Vb0	Breakover voltage, is measured at 100V/ $\mu s.$	Іво	Breadover current.
Co	Off-state capacitance ismeasured in VDC=2V@1MHz.	Iτ	ON-state current
IDRM Leakage current, is measured at VDRM.		Vт	On-state voltage.

Part Numbering System

<u>BE</u> P	0080	M	<u>A</u>
(A)	(B)	(C)	(D)

- (A) BORN's Semiconductor Surge Arrester
- (B) Series:0080
- (C) Pake:SOD123
- (D) Rating Sure Voltage:A:2KV(10/700µs)



Electrical Characteristics Curves

Figure1 V-I Characteristics

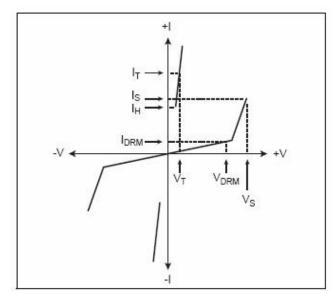
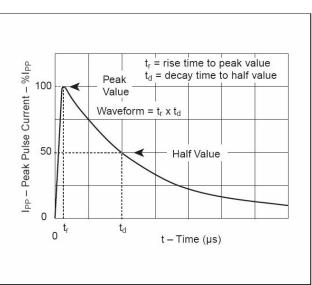
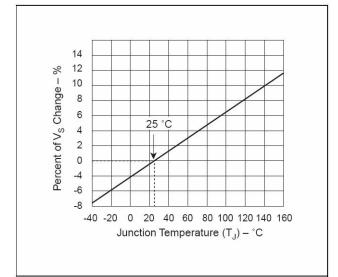
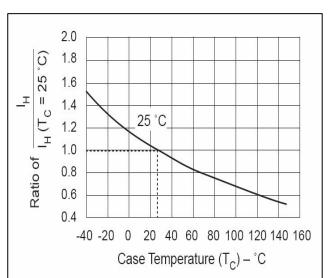


Figure 3Normalized Vs Change versusJunctionTemperature







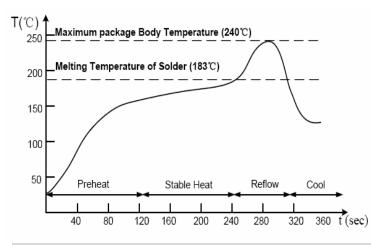


Thermal Considerations

Package SOD123	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature	-40 to +150	°C
	Ts	Storage Temperature Range	-40 to +150	°C
	R _{θJA}	Junction to Ambient on printed circuit	90	°C/W

Figure2 tr x td Pulse Wave-form

Solder Reflow Recommendations



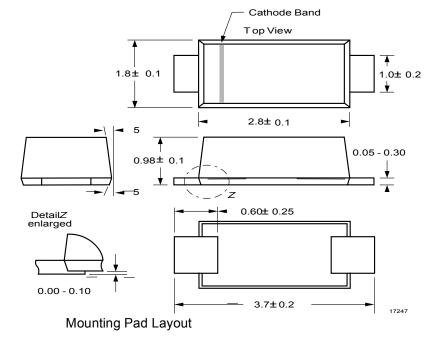
Product Dimensions

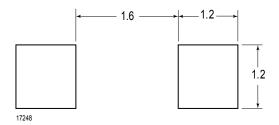
4/4 -

- Recommended reflow methods: IR, vapor phase oven, hot air oven, wave solder.
- The device can be exposed to a maximum temperature of 265°C for 10 seconds.
- Devices can be cleaned using standard

industry methods and solvents.

Notes: If reflow temperatures exceed the recommended profile, devices may not meet the performance requirements.





X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Gas Discharge Tubes - GDTs / Gas Plasma Arrestors category:

Click to view products by Bourne manufacturer:

Other Similar products are found below :

 PMT1023004
 PMT1025001
 PMT1035004
 PMT1040004
 PMT809006
 CG2250
 CG2800
 CG31.5L
 GT-SMD181240012-TR
 WPGT

 2N145B6L
 WPGT-2N230B6L
 WPGT-2N470B6L
 WPGT-2R470B6L
 WPGT-2RM230A6L
 WPGT-2RM350A6L
 WPGT-2RM70A6L

 WPGT-2RM90A6L
 WPGT-2S145
 WPGT-2S350
 WPGT-2S470
 WPGT-3R350CF
 WPGT-3R350G1
 WPGT-3R90G1
 WPGT-3R75G1

 WPGT-3R470G1
 WPGT-3R250C
 WPGT-3R230G1
 WPGT-2S230
 WPGT-2RM470A6L
 WPGT-2RM145A6L
 WPGT-2R3000B8L
 WPGT

 2R2700B8L
 WPGT-2R1000B8L
 WPGT-2N90B6L
 WPGT-2N70B6L
 WPGT-2N350B6L
 WPGT-2N230B6L1
 CG90
 CG2230
 CG2145

 CG21000
 GT-SMD181215012-TR
 T61-C350X
 9071.99.0547 (73_Z-0-0-547)
 B88069X6940B152
 9071.99.0052(73_Z-0-0-52)

 B88069X1973T902
 A9L15692
 C50-0-255
 A9L16294